

ma-N 1410 – run sheet

micro resist technology GmbH

nanyte.com/photoresists/ma-n-1410 · last updated 2026-07-26

Thickness: 1 µm

Softbake: 100 °C · 1.5 min · hotplate

Exposure dose: 450 mJ/cm²

Develop: Developer ma-D 533/S · Time 30 s (20–40 s) · Rinse
Developed resist films are thoroughly rinsed with deionized water and then dried. · Method immersion

Hardbake: 100 °C · 30 min